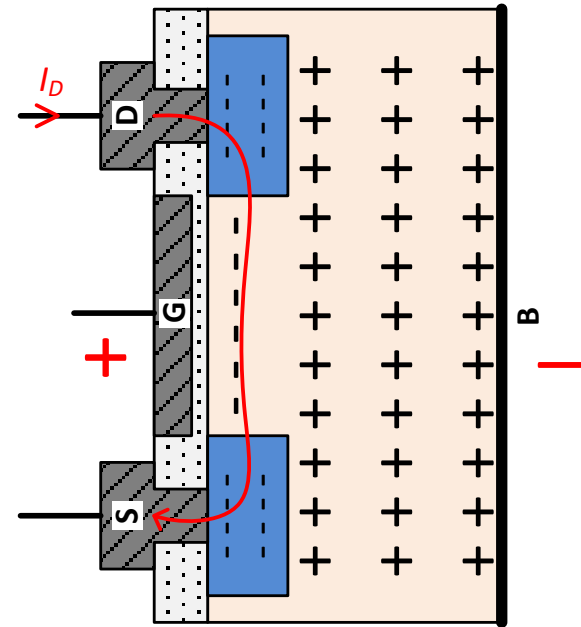
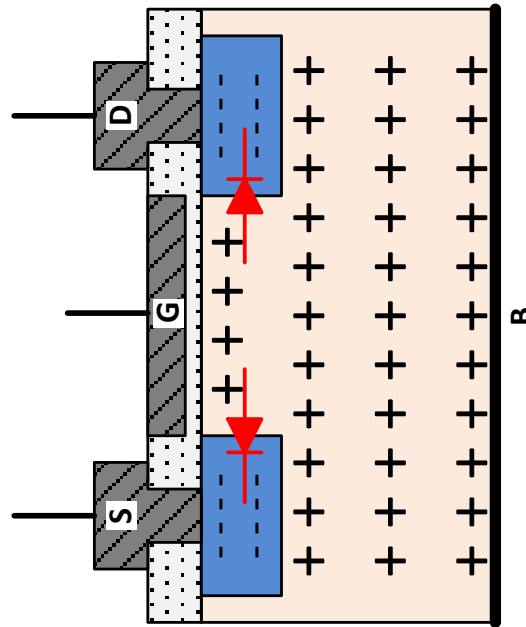
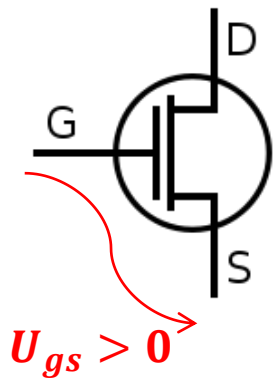
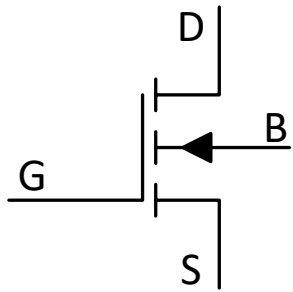


Osnove mikroprocesorske elektronike

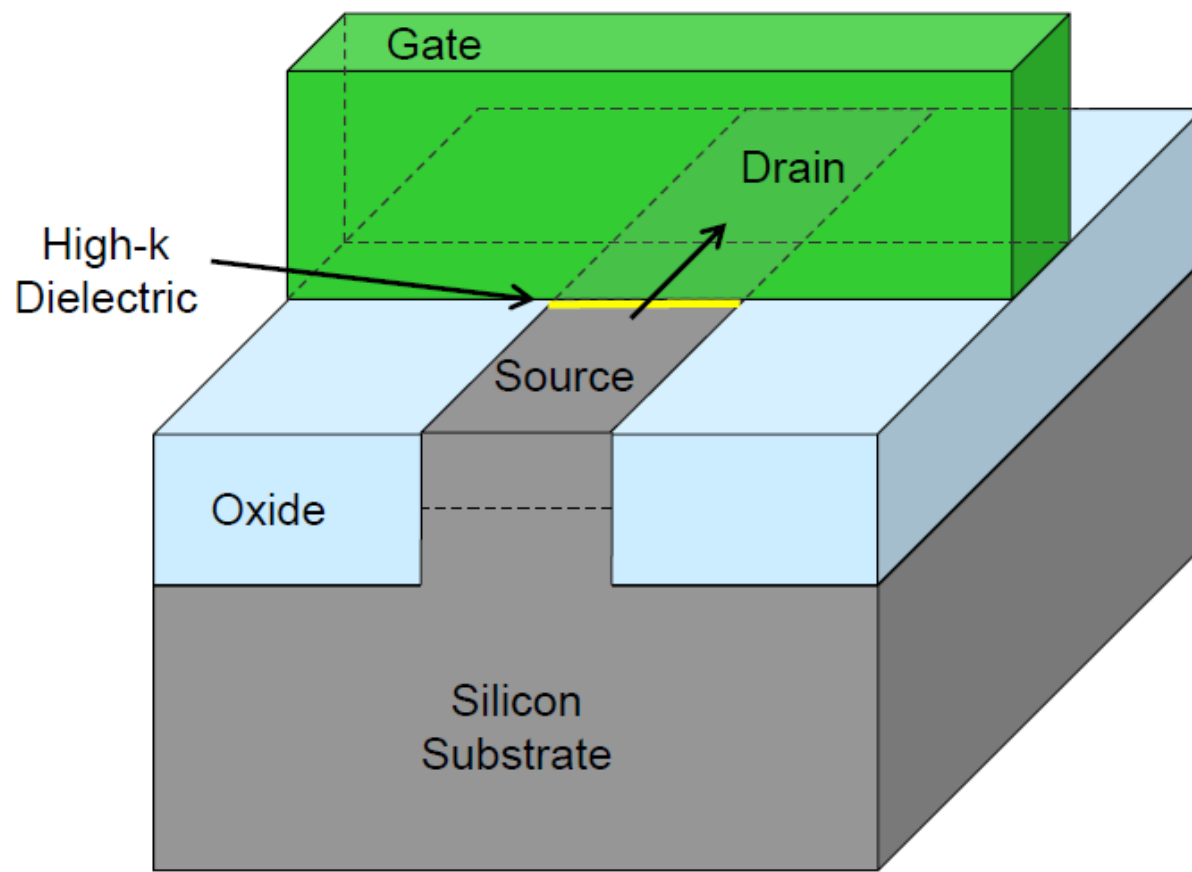
Marko Jankovec

MOS transistor – osnovni gradnik mikroprocesorjev

Osnovni element – nMOS tranzistor

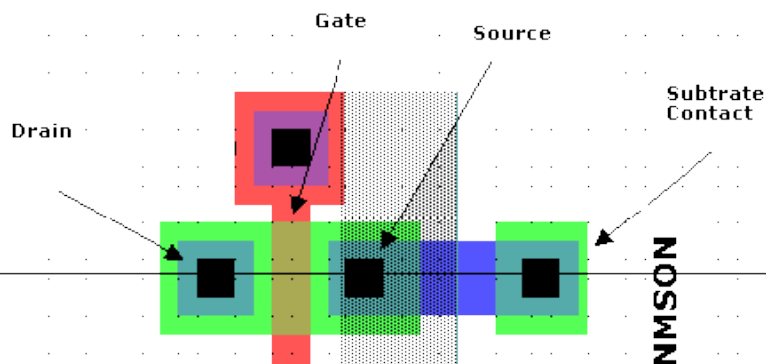


MOS tranzistor

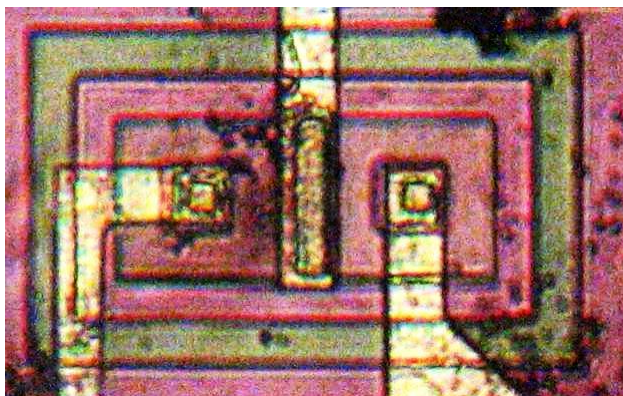


MOS tranzistor

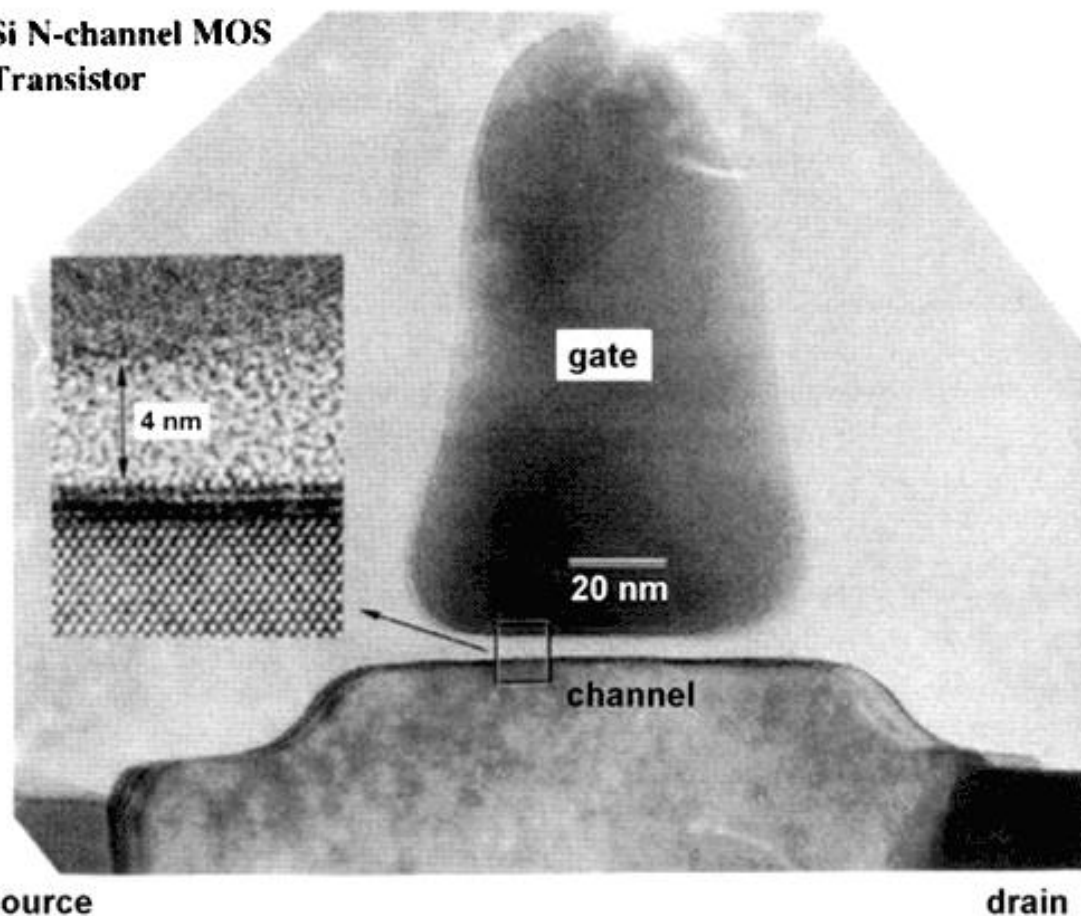
http://www.youtube.com/watch?v=v7J_snw0Eng



<http://www.ami.ac.uk>



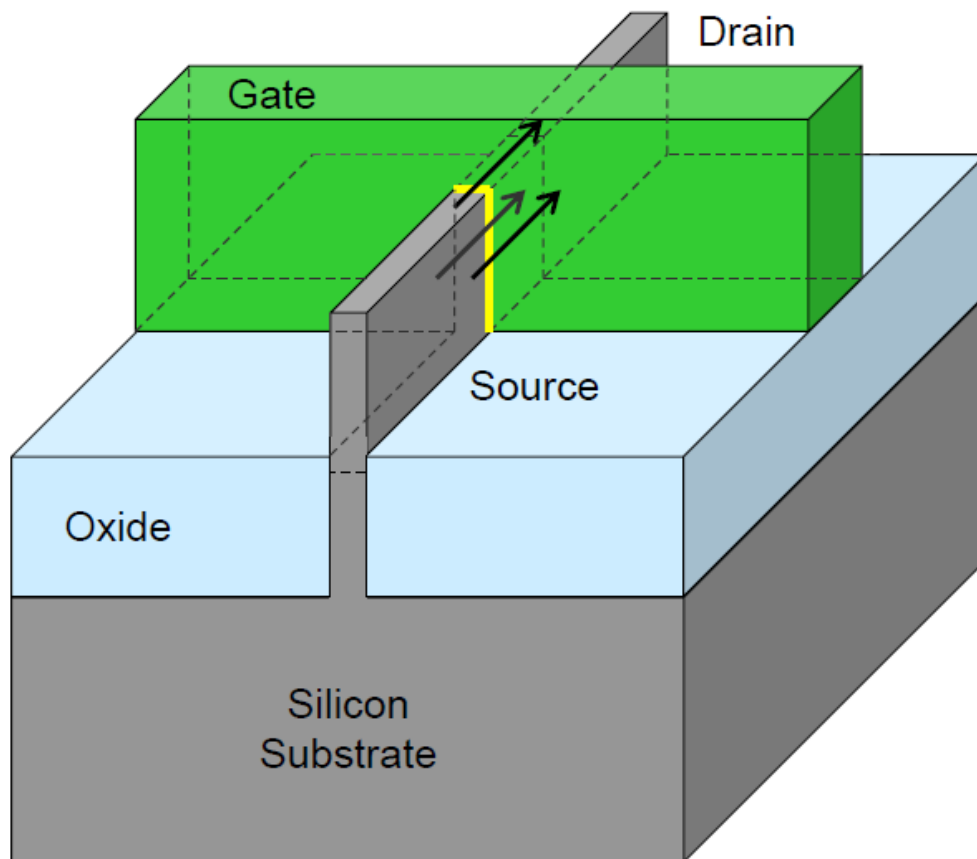
Si N-channel MOS Transistor



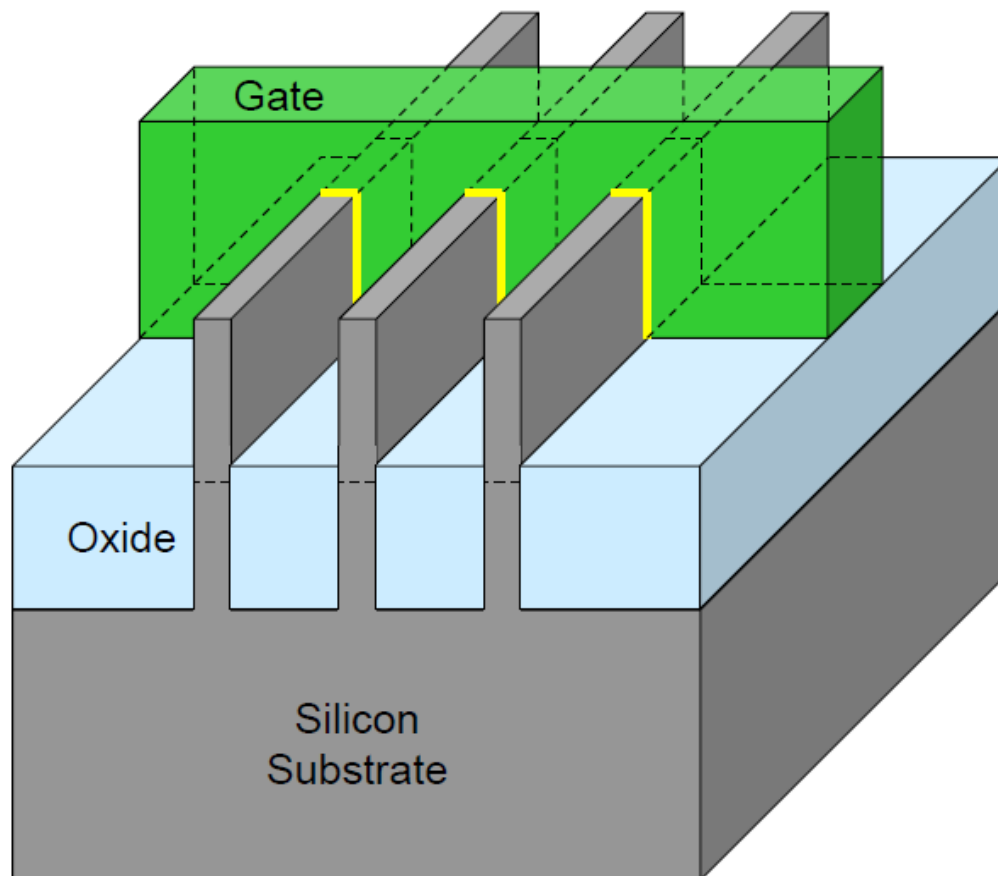
http://uvicrec.blogspot.com/2011_09_01_archive.html

www.chem.wisc.edu

3D Tri-Gate MOS tranzistor

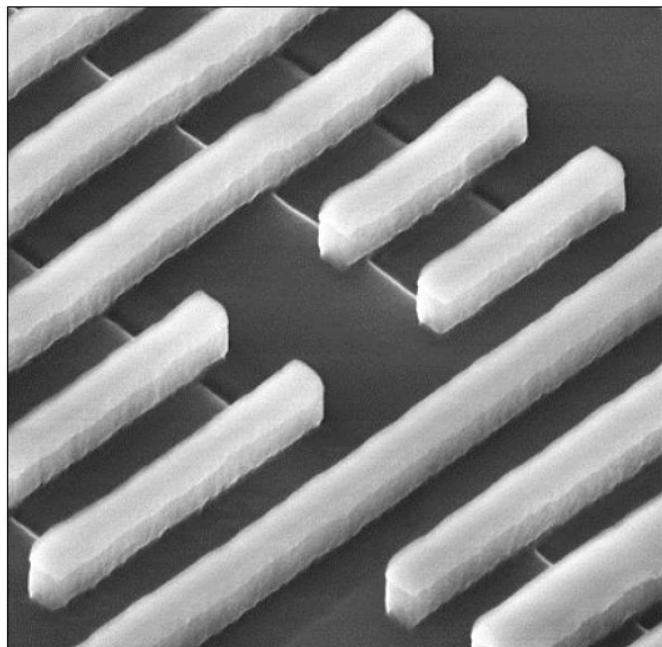


3D Tri-Gate MOS tranzistor

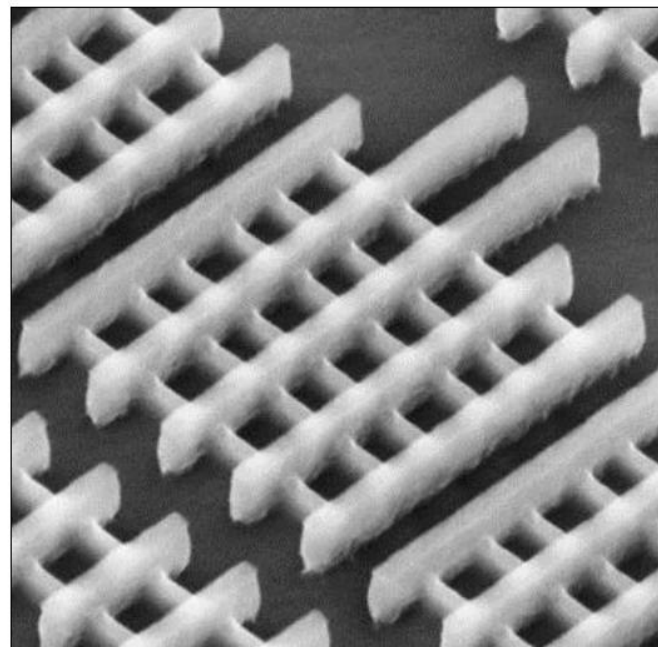


Primerjava

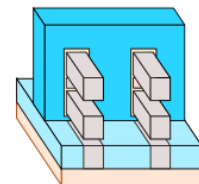
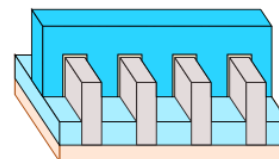
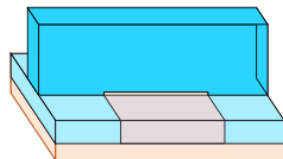
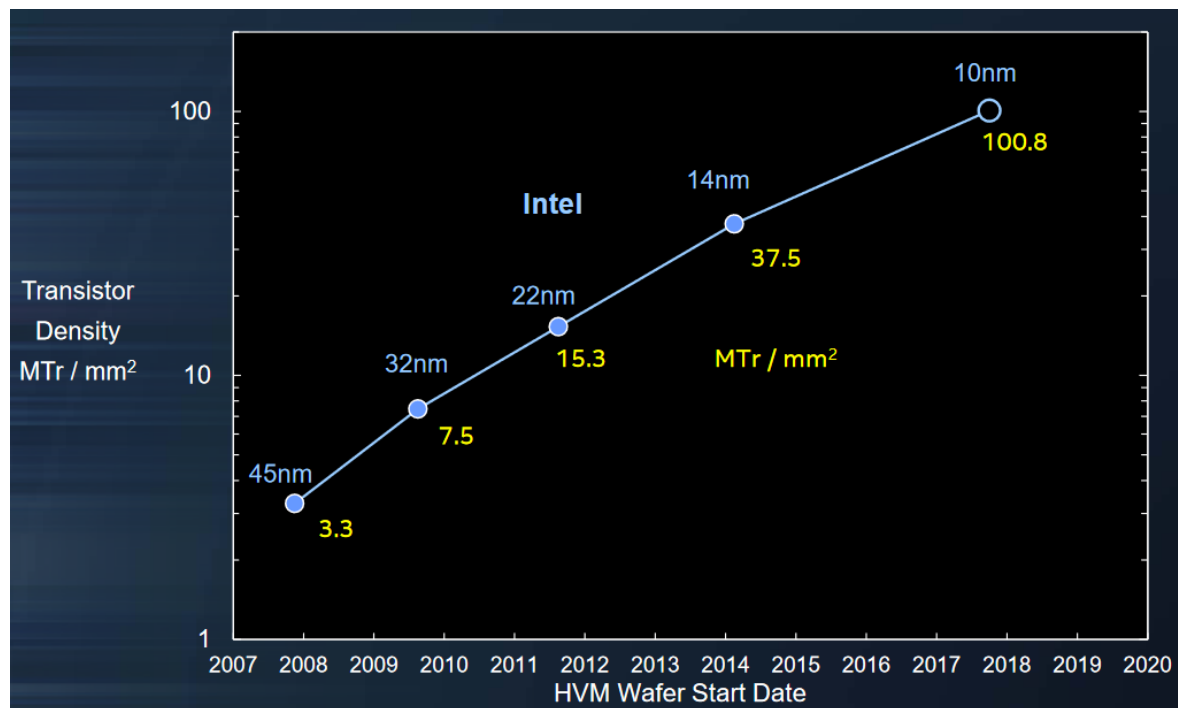
32 nm planarni MOS tranzistor



22 nm Tri-Gate MOS tranzistor



Moorov zakon za gostoto tranzistorjev



90nm

65nm

45nm

32nm

22nm

14nm

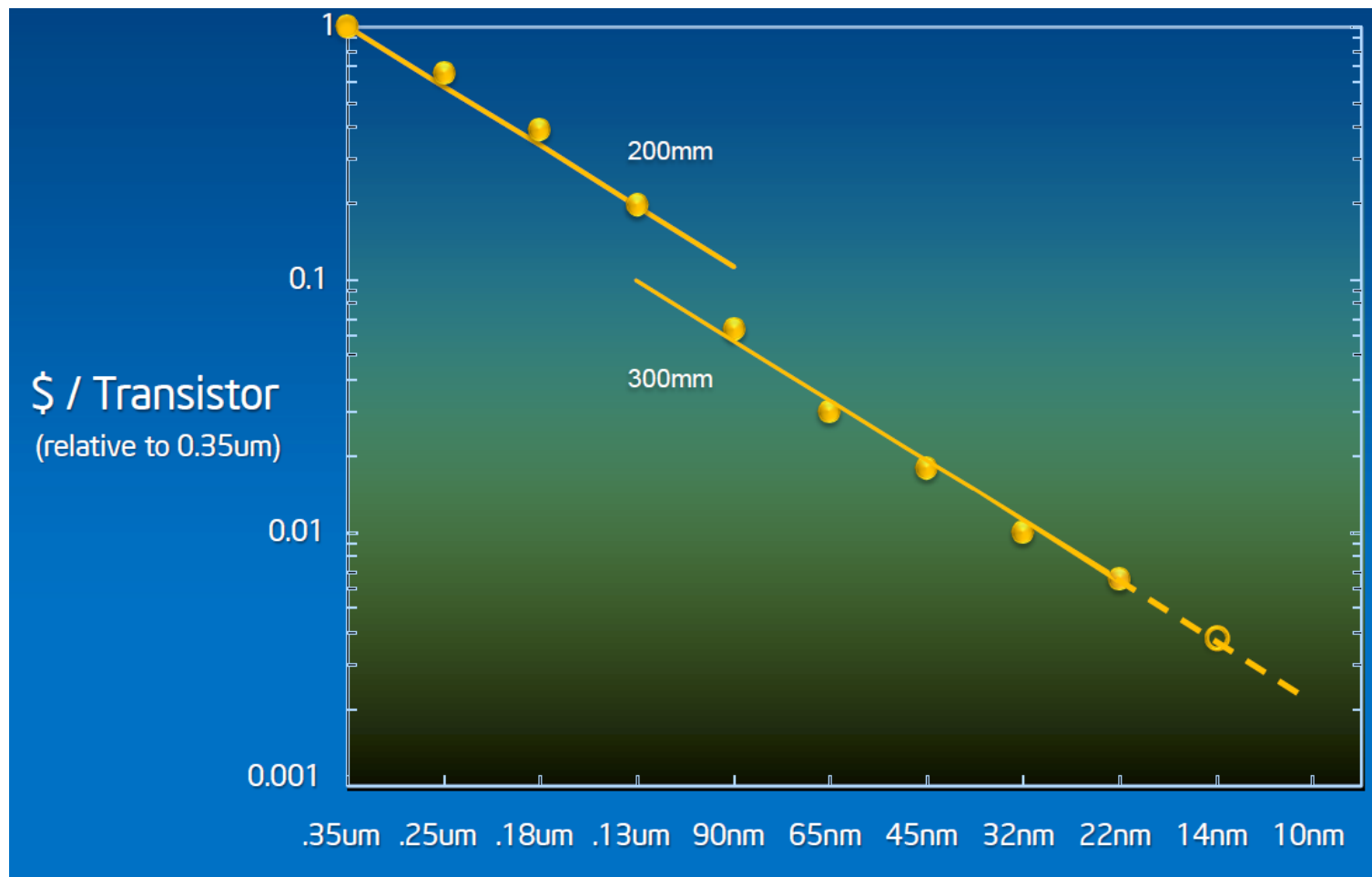
10nm

7nm

5nm

3nm

Moorov zakon za ceno tranzistorjev

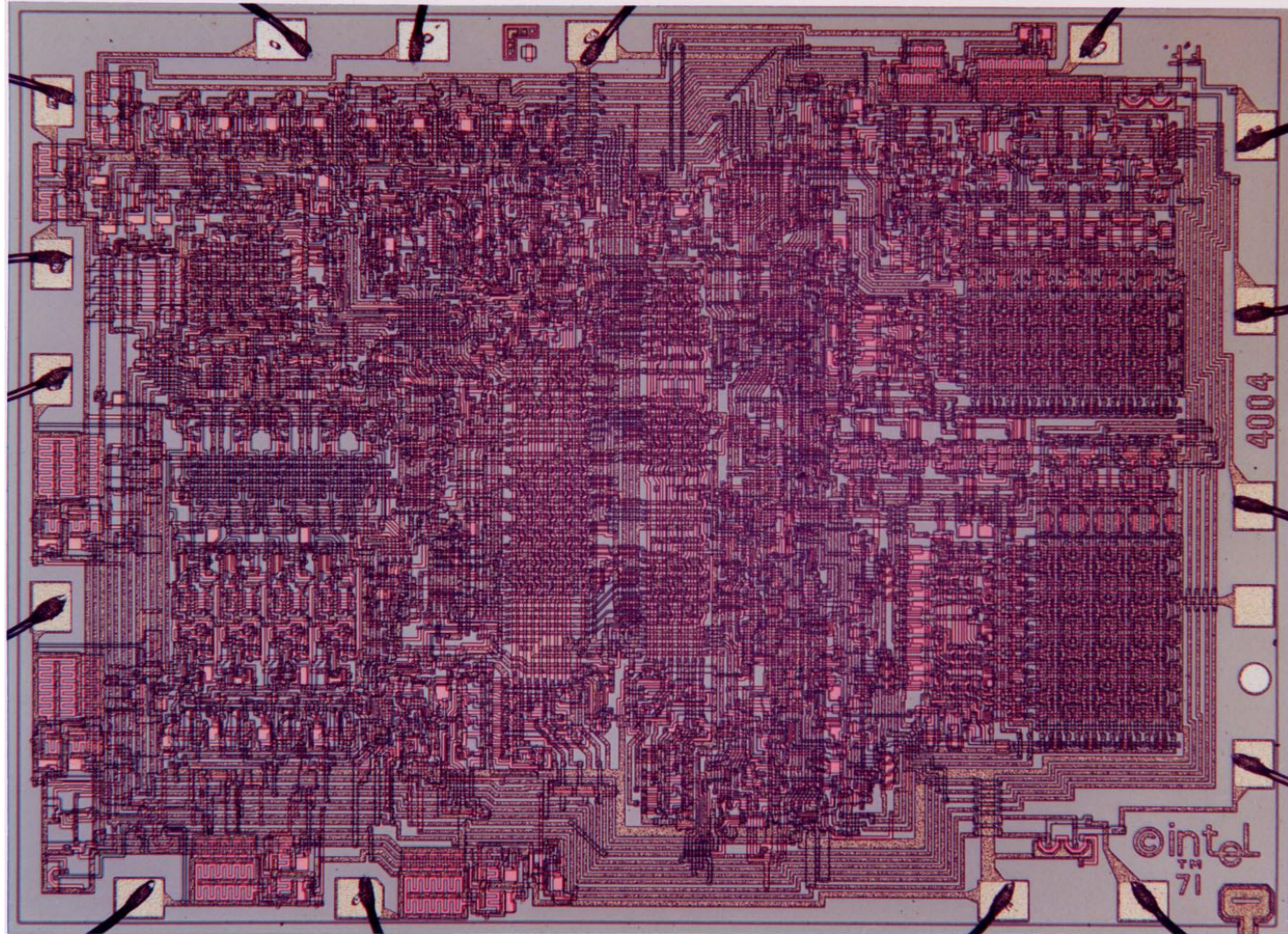


Osnove mikroprocesorske elektronike

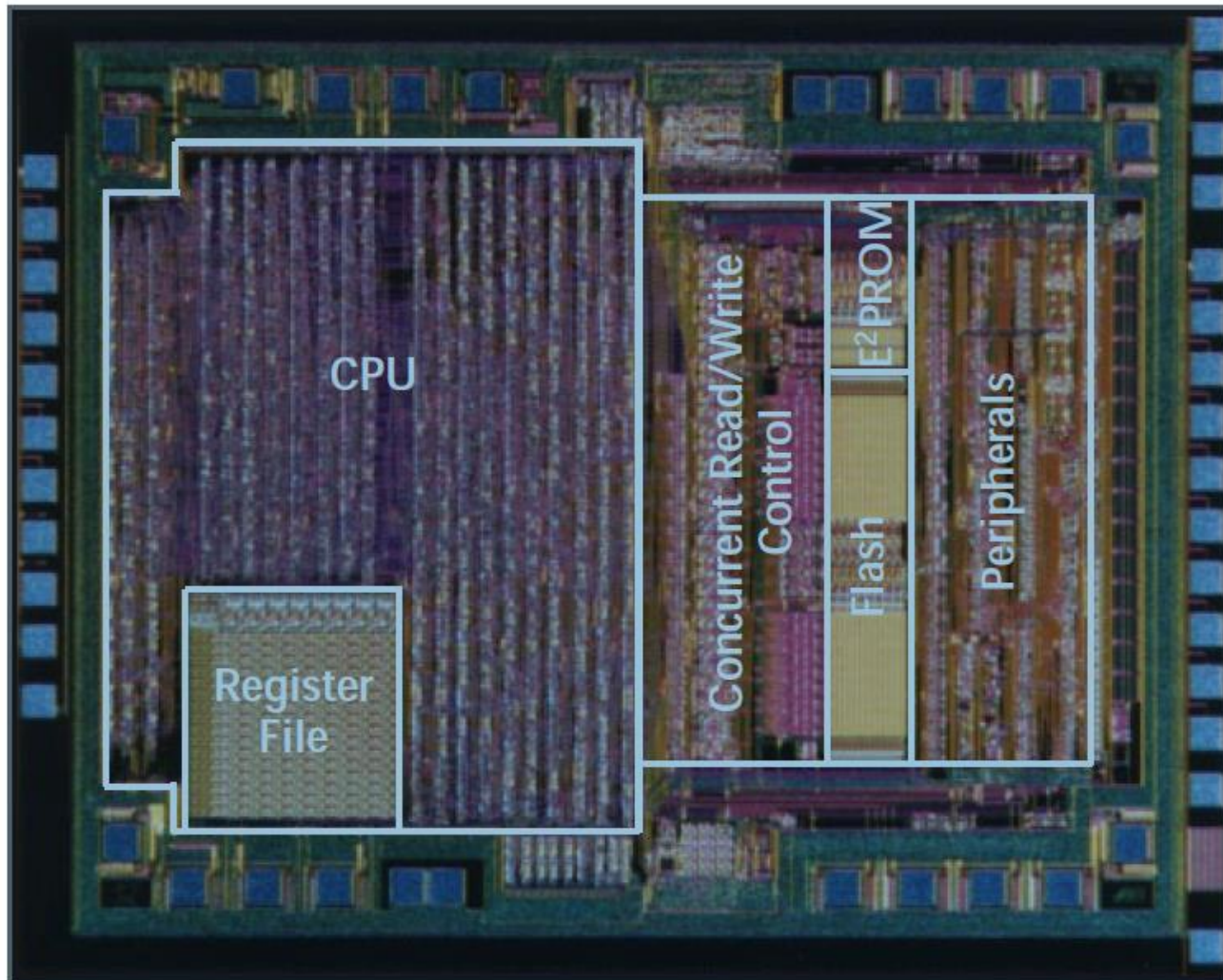
Marko Jankovec

Pomnilniki v mikrokrmilniku

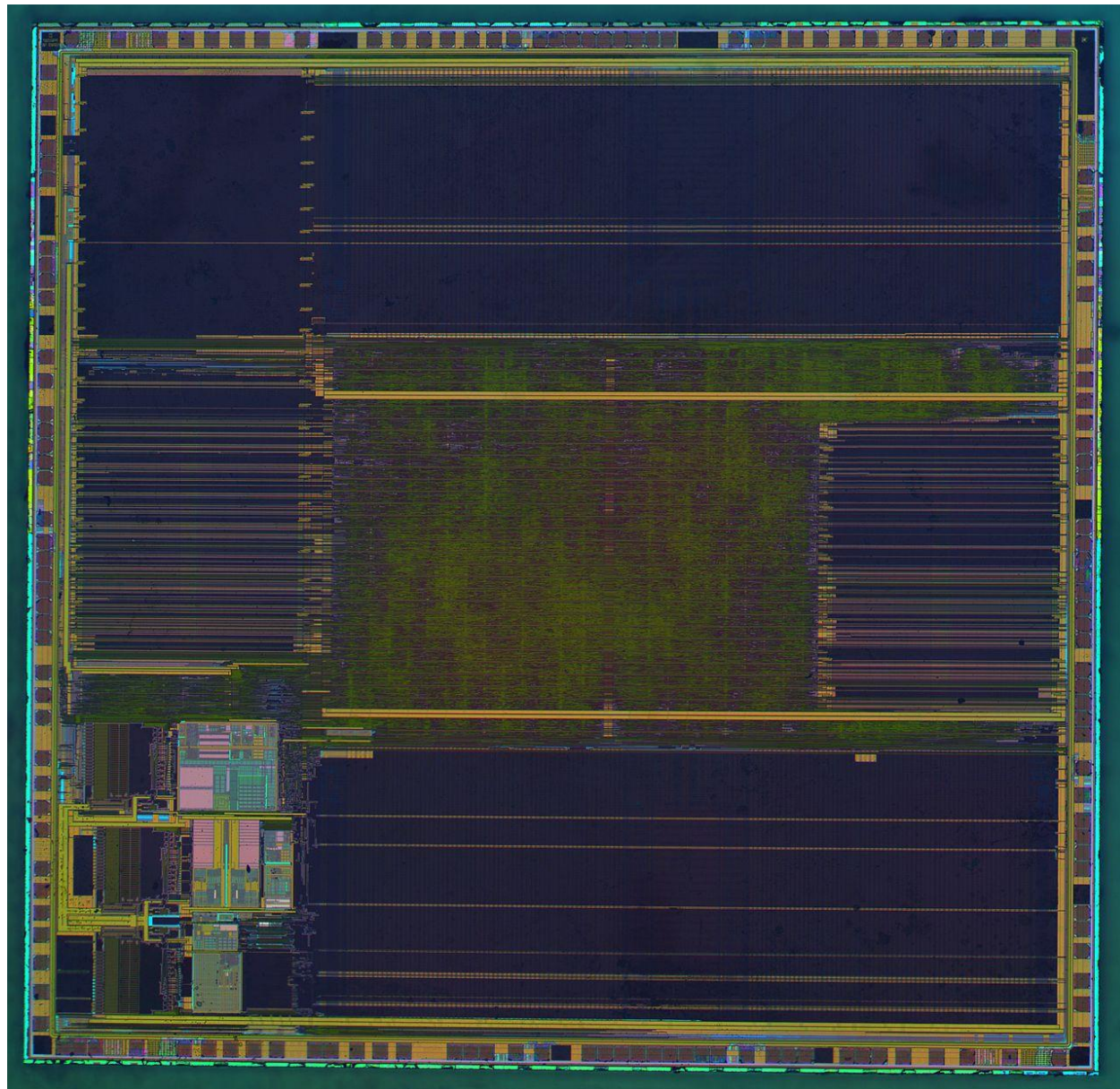
Intel 4004



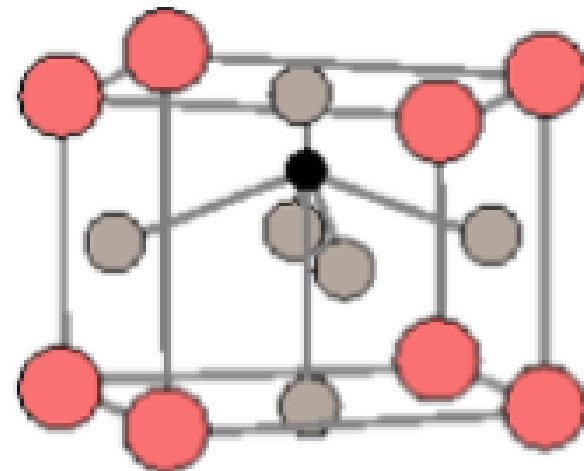
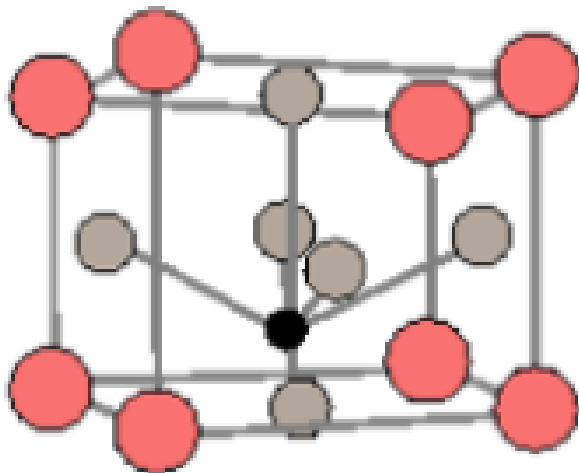
AT90S1200



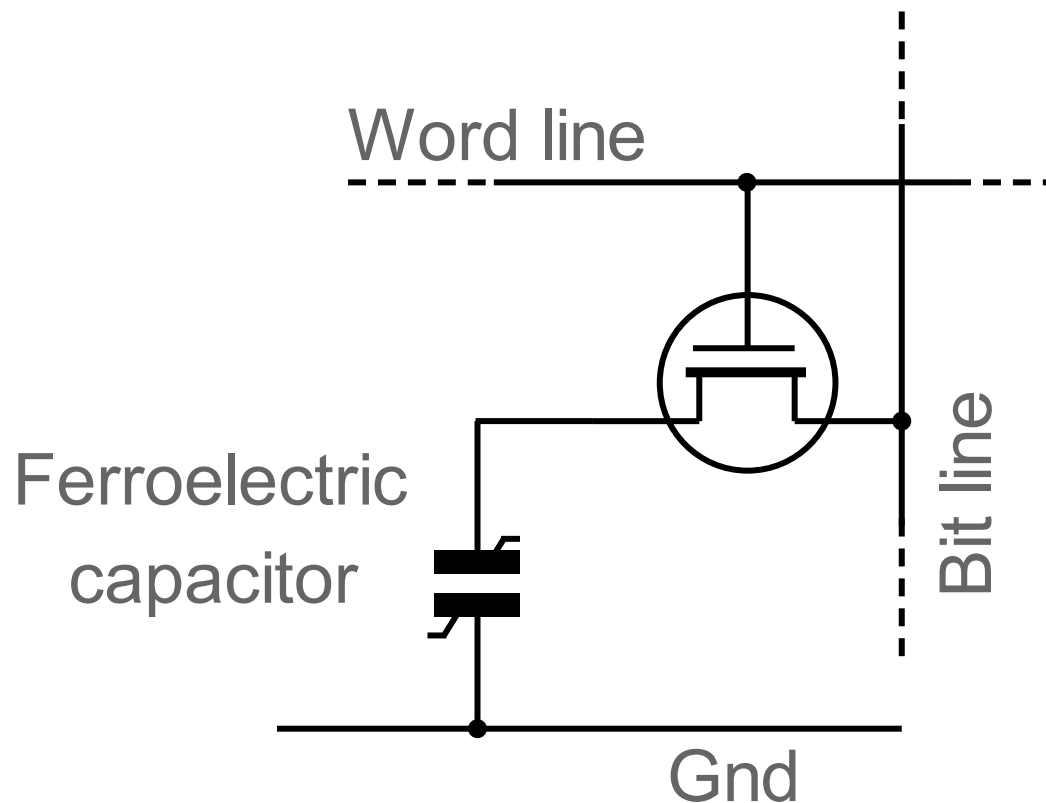
STM32F100



FRAM – Feroelektrični materiali



FRAM – variabilni kondenzator



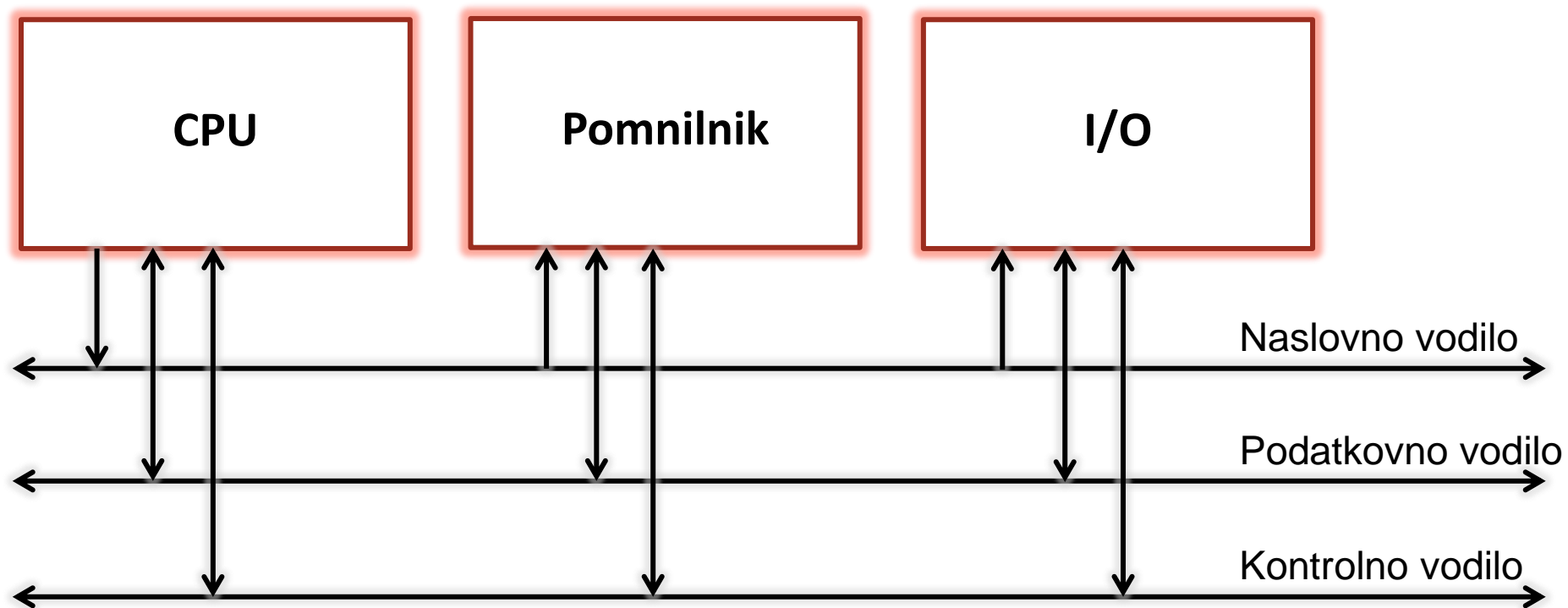
Primerjava

	FRAM	SRAM	Flash	EEPROM
Non-Volatile Retains data without power	Yes	No	Yes	Yes
Avg Active Power ($\mu\text{A}/\text{MHz}$)	100	< 60	230	50,000+
Write Power for 12KB/s	9 μA	N/A	2200 μA	N/A
Write Speeds (13KB)	10 ms	< 10 ms	1 sec	2 secs
Write Endurance	10^{15}	Unlimited	10^5	10^5
Bit-wise Programmable	Yes	Yes	No	No
Data Erase Required	No	No	Segment	Page
Unified: Code and Data	Yes	No	No	No
Read Speeds	8 MHz	up to 25MHz (on some devices)		N/A

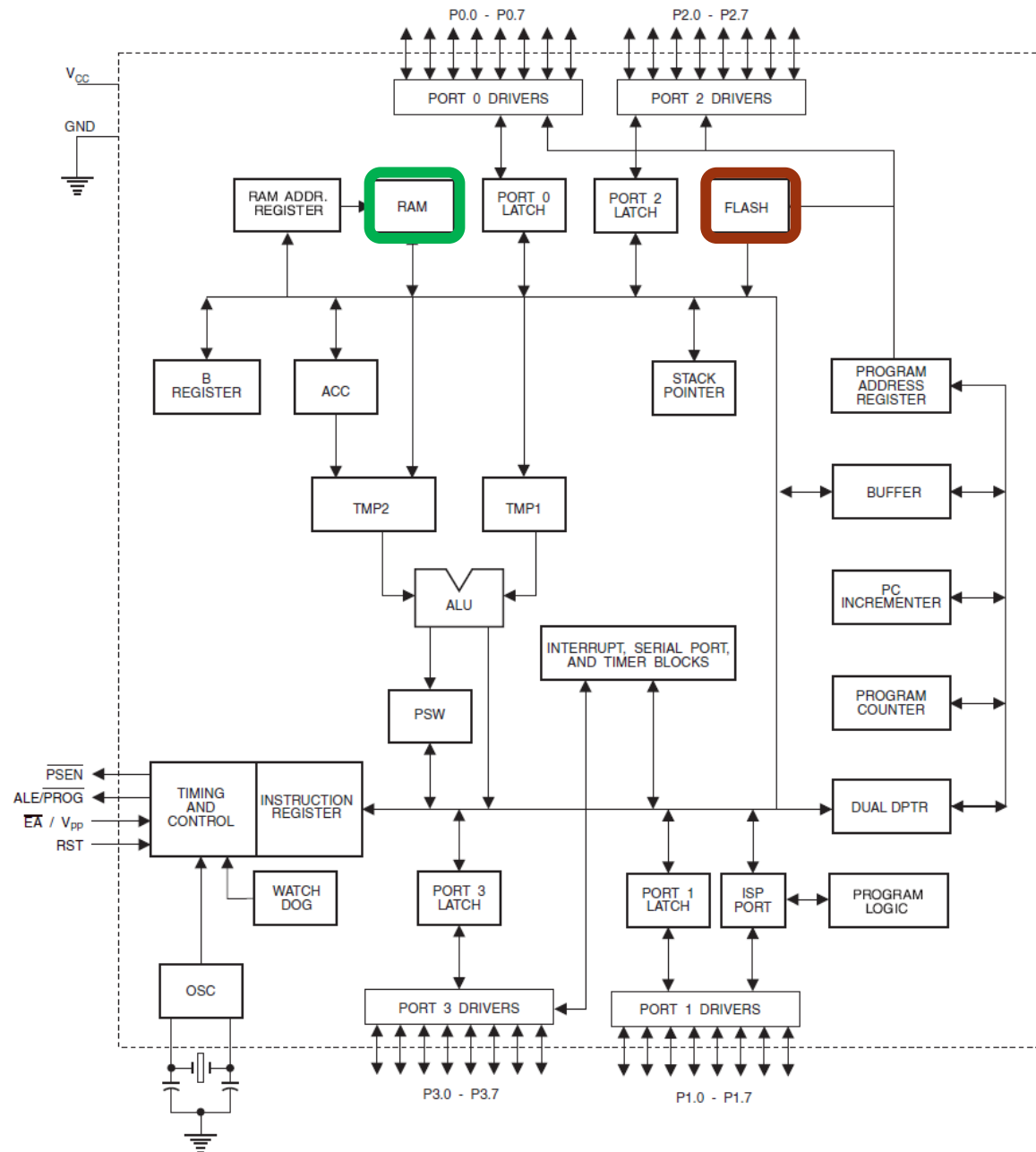
- Similar to SRAM, FRAM has virtually unlimited write endurance with no signs of degradation. FRAM does not require a pre-erase in which every write to FRAM is non-volatile. However, there are some minor trade-offs in using FRAM instead of RAM that may apply to a subset of use cases. One of the differences on the MSP430 platform is the FRAM access speed, which is limited to 8 MHz, whereas, SRAM can be accessed at the maximum device operating frequency. Wait-states are required if the CPU accesses the FRAM at speeds faster than 8 MHz. Another trade-off is that FRAM access results in a somewhat higher power consumption compared with SRAM.

- Variables are allocated in SRAM by the default linker command files. FRAM-based MSP430 devices would typically have 2KB of SRAM. For the exact specification, see the device-specific data sheet. If the variable size is too large to fit in SRAM, the linker command file can be modified or C-language `#pragma` directives can be used to allocate specific variables or structures in FRAM memory. Section 3.4 showcases how you would modify the linker command file to move variables from SRAM to FRAM. Aside from SRAM memory constraint, another reason you would use FRAM for variables is to decrease start-up time as outlined in Section 4.

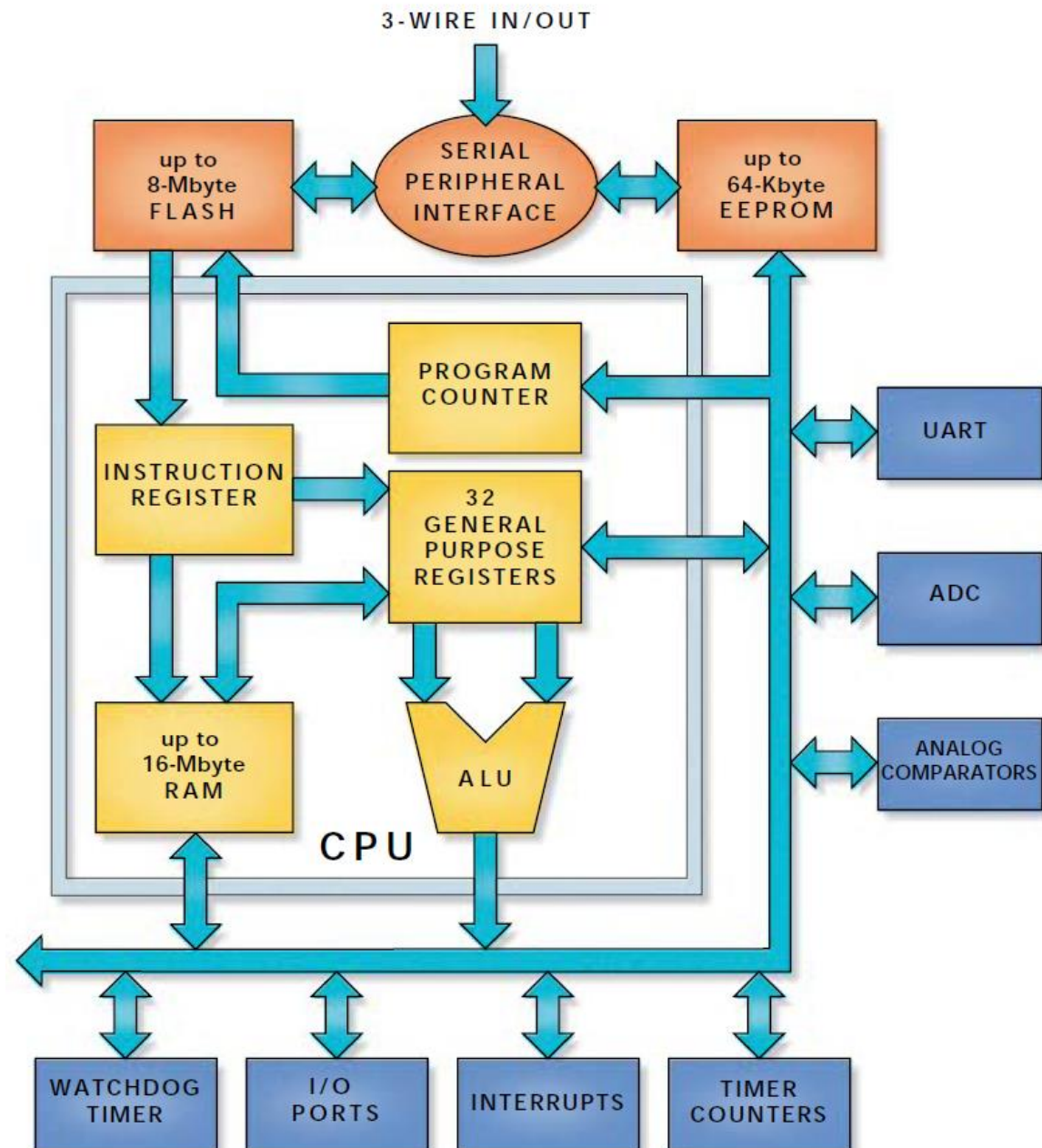
Mikroračunalnik (MCU)



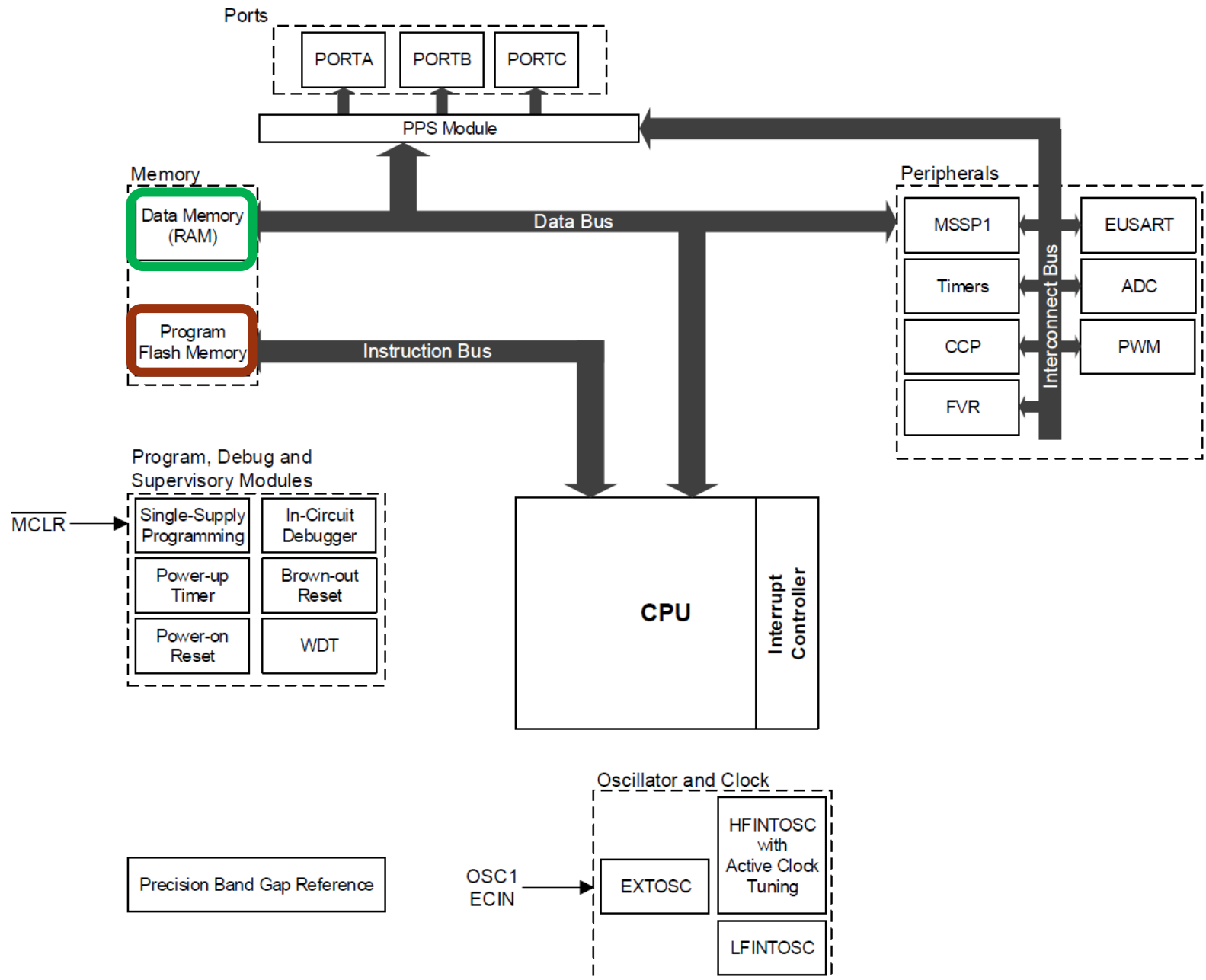
8051



AVR



PIC



STM

